



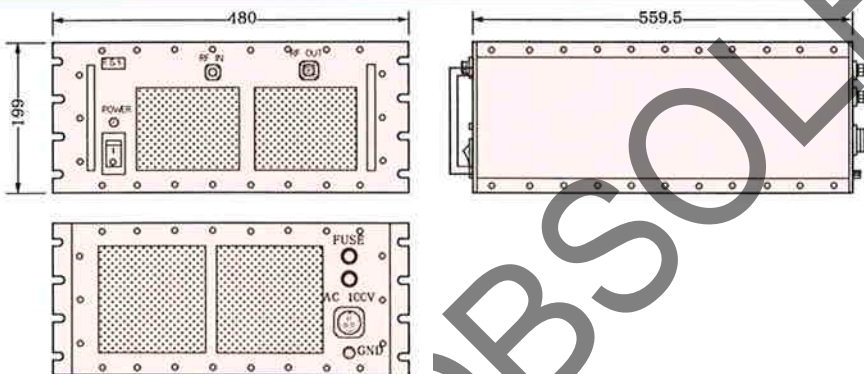
MICROWAVE GaAs FET AMPLIFIER

MODEL R&K A2000-50-R

- BROADBAND FREQUENCY : 1000~2000MHz
- HIGH POWER : 50W min. (@1dB Comp.)
- HIGH RELIABILITY GaAs FET CONSTRUCTION
- FOR COMMUNICATIONS TEST EQUIPMENT



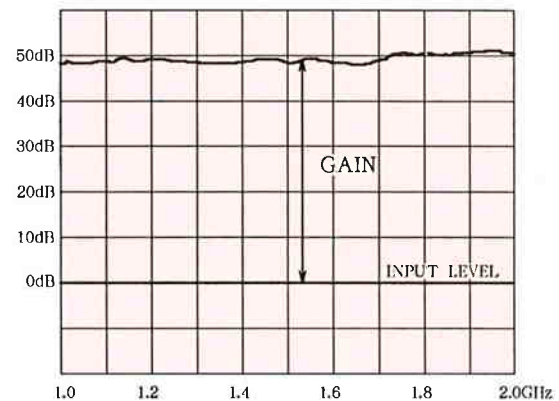
DIMENSION



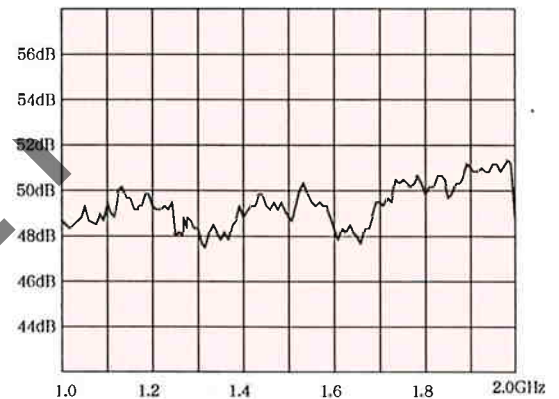
SPECIFICATIONS

- | | |
|-------------------------------------|--|
| 1. Input/Output Frequency Range | 1000~2000MHz (min.) |
| 2. Small Signal Gain | +47dB (min.) |
| 3. Power Gain @1dB Compression | +46dB (min.) |
| 4. Power Gain Flatness | ±2.0dB (max.) |
| 5. Power Output (@1dB Comp.) | 50W (min.) |
| 6. Amplifier Operation Mode | Class A Linear |
| 7. 2 Tone 3rd Order Intercept Point | +57dBm (typ.) |
| 8. Input/Output Impedance | 50 Ω Nominal |
| 9. Input VSWR | 2.0 (max.) |
| 10. Output VSWR | 1.5 (max.) |
| 11. Harmonics | -18dBc (max.) @ Full Power |
| 12. Spurious | -60dBc (max.) @ Full Power |
| 13. Input Noise Figure | 10.0dB (typ.) |
| 14. Output Power Duty Ratio | 100 % C.W. |
| 15. Connectors | RF Input
RF Output
N - Female |
| 16. AC Power Supply Input | 100V, AC · 50/60Hz · 15A (max.) |
| 17. Cooling | Integral Forced Air Cooling |
| 18. Operating Temperature | -10 °C ~ +45 °C |
| 19. Storage Temperature | -15 °C ~ +65 °C |
| 20. Protection Circuits | Infinite Load VSWR
Thermal Overload |

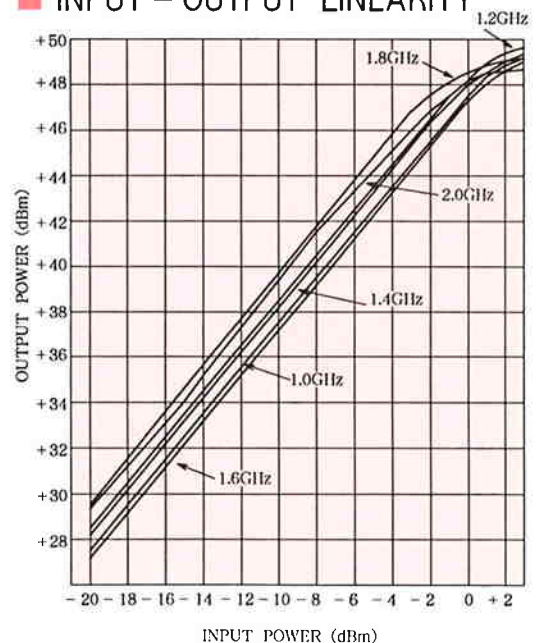
SMALL SIGNAL GAIN



GAIN FLATNESS



INPUT - OUTPUT LINEARITY



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